

RJF0609JSP

60V - 1.5V Silicon N Channel Thermal FET Power Switching R07DS1066EJ0200 Rev.2.00 Jan 15, 2016

Datasheet

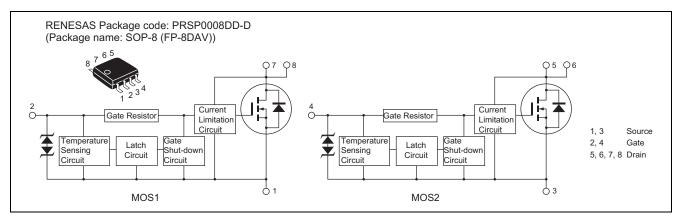
Description

This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

Features

- Logic level operation (4 V Gate drive).
- Built-in the over temperature shut-down circuit.
- High endurance capability against to the short circuit.
- Latch type shut down operation (need 0 voltage recovery).
- Built-in the current limitation circuit.
- High density mounting
- Power supply voltage applies 12 V and 24 V.
- AEC-Q101 Compliant

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$ Unit ltem Symbol Ratings Drain to source voltage VDSS 60 V Gate to source voltage VGSS 16 V Gate to source voltage VGSS V -2.5 D Note4 Drain current 1.5 А Body-drain diode reverse drain current IDR 1.5 A IAP Note 3 Avalanche current 1.5 A EAR Note 3 Avalanche energy m.J 9.6 Pch Note 1 Channel dissipation W 1 Pch Note 2 Channel dissipation 1.5 W Channel temperature Tch °C 150 °C Storage temperature Tstg -55 to +150

Notes: 1. 1 Drive operation : When using the glass epoxy board (FR4 $40 \times 40 \times 1.6$ mm), PW ≤ 10 s

2. 2 Drive operation : When using the glass epoxy board (FR4 40 \times 40 \times 1.6 mm), PW \leq 10 s

3. Tch = 25°C, Rg \geq 50 Ω

4. It provides by the current limitation lower bound value.



Typical Operation Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input voltage	VIH	3.5			V	
	VIL	_		1.2	V	
Input current	IIH1			100	μA	Vi = 8 V, V _{DS} = 0
(Gate non shut down)	I _{IH2}			50	μA	Vi = 3.5 V, V _{DS} = 0
	١L			1	μA	Vi = 1.2 V, V _{DS} = 0
Input current	I _{IH(sd)1}		0.8		mA	Vi = 8 V, V _{DS} = 0
(Gate shut down)	I _{IH(sd)2}	_	0.35		mA	$Vi = 3.5 V, V_{DS} = 0$
Shut down temperature	Tsd		175		°C	Channel temperature
Gate operation voltage	Vop	3.5		12	V	
Drain current (Current limitation value)	I _{D limt}	1.5			A	V_{GS} = 5 V, V_{DS} = 10 V ^{Note 5}

Notes: 5. Pulse test

Electrical Characteristics

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain current				5.4	A	$V_{GS} = 3.5 \text{ V}, \text{ V}_{DS} = 10 \text{ V}^{\text{Note 6}}$
				10	mA	$V_{GS} = 3.3 V, V_{DS} = 10 V$ $V_{GS} = 1.2 V, V_{DS} = 10 V$
	ID2 ID3	1.5			A	$V_{GS} = 1.2 V, V_{DS} = 10 V$ $V_{GS} = 12 V, V_{DS} = 10 V^{Note 6}$
Drain to source breakdown	V _{(BR)DSS}	60			X V	$V_{GS} = 12 \text{ V}, \text{ V}_{DS} = 10 \text{ V}$ $I_D = 10 \text{ mA}, \text{ V}_{GS} = 0$
voltage	V (BR)D55	00			v	$\mathbf{U} = 10 \mathbf{m} \mathbf{A}, \mathbf{VGS} = 0$
Gate to source breakdown	V _{(BR)GSS}	16	_	_	V	$I_G = 800 \ \mu A, \ V_{DS} = 0$
voltage	V _(BR) GSS	-2.5	_	—	V	$I_G = -100 \ \mu A, V_{DS} = 0$
Gate to source leak current	Igss1		_	100	μA	$V_{GS} = 8 V, V_{DS} = 0$
	Igss2		_	50	μA	$V_{GS} = 3.5 V, V_{DS} = 0$
	Igss3		—	1	μA	V _{GS} = 1.2 V, V _{DS} = 0
	Igss4		—	-100	μA	$V_{GS} = -2.4 \text{ V}, V_{DS} = 0$
Input current (shut down)	IGS(OP)1		0.8	—	mA	$V_{GS} = 8 V, V_{DS} = 0$
	IGS(OP)2		0.35	—	mA	$V_{GS} = 3.5 V, V_{DS} = 0$
Zero gate voltage drain current	IDSS		—	10	μΑ	$V_{DS} = 32 V, V_{GS} = 0$
						Ta = 125°C
Gate to source cutoff voltage	VGS(off)	1.1	_	2.1	V	$I_D = 1 \text{ mA}, V_{DS} = -0 \text{ V}$
Forward transfer admittance	y _{fs}	1.0	2.2	—	S	$I_D = 0.75 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note 6}}$
Static drain to source on state	R _{DS(on)}		208	350	mΩ	$I_D = 0.75 \text{ A}, V_{GS} = 4 \text{ V}^{\text{Note 6}}$
resistance	R _{DS(on)}		142	263	mΩ	$I_D = 0.75 \text{ A}, V_{GS} = 10 \text{ V}^{Note 6}$
Output capacitance	Coss		265	_	pF	$V_{DS} = 10 V, V_{GS} = 0, f = 1MHz$
Turn-on delay time	t _{d(on)}		0.55	_	μS	I _D = 0.7 A, V _{GS} = 10 V
Rise time	tr		1.88	_	μS	$R_L = 43 \Omega$
Turn-off delay time	t _{d(off)}	_	3.9	—	μS	
Fall time	t _f	_	3.7	—	μS	
Body-drain diode forward voltage	V _{DF}	_	0.82	—	V	$I_F = 1.5 \text{ A}, \text{ V}_{GS} = 0$
Body-drain diode reverse	trr	_	71	—	ns	$I_F = 1.5 \text{ A}, V_{GS} = 0$
recovery time						di _F /dt = 50 A/µs
Over load shut down	t _{os1}	_	1.02		ms	$V_{GS} = 5 \text{ V}, V_{DD} = 16 \text{ V}$
operation time Note 7	t _{os2}	_	0.59	_	ms	$V_{GS} = 5 V, V_{DD} = 24 V$

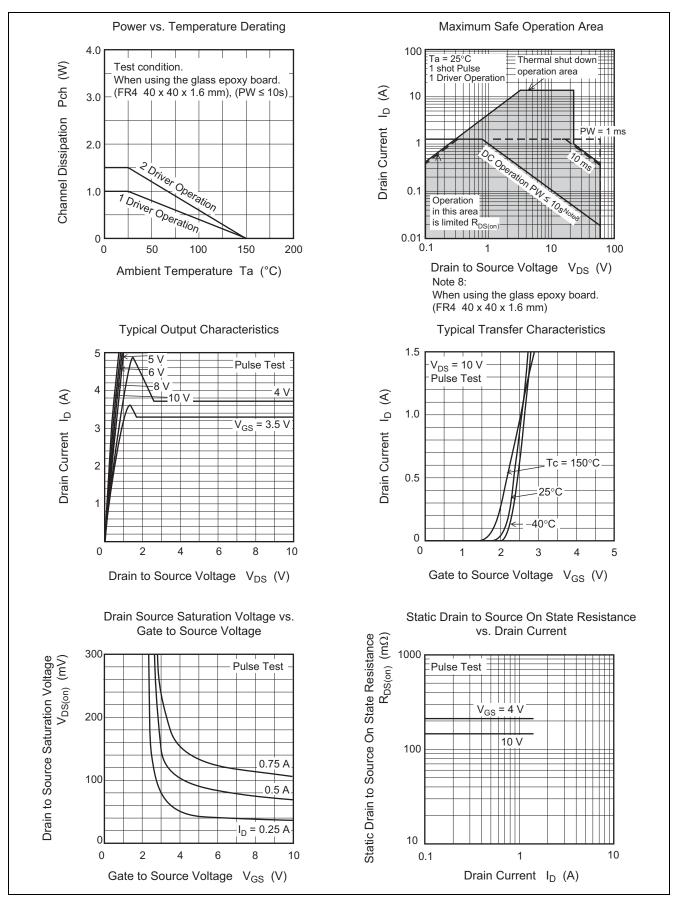
Notes: 6. Pulse test

7. Including the junction temperature rise of the over loaded condition.

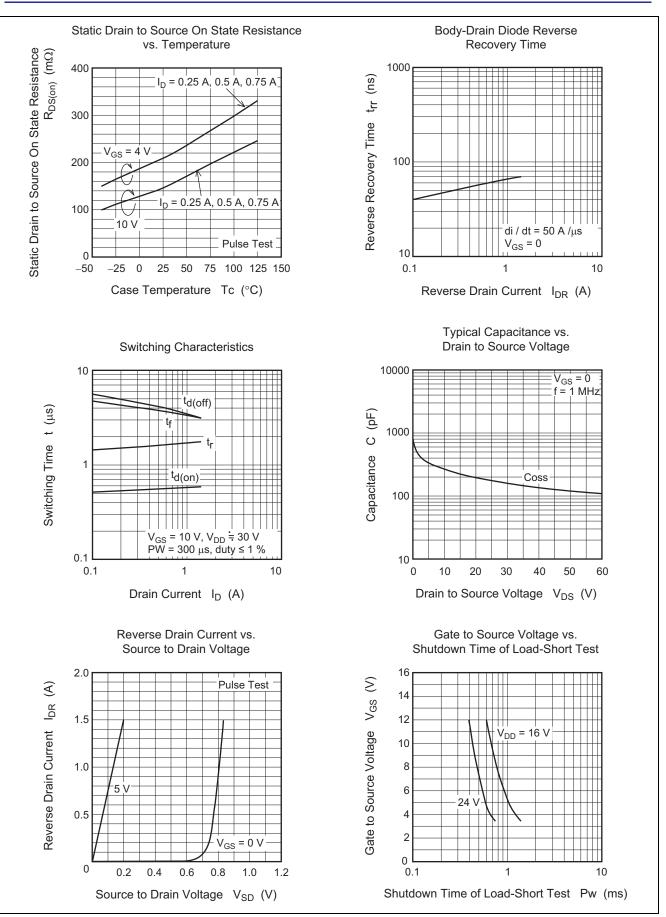
R07DS1066EJ0200 Rev.2.00 Jan 15, 2016



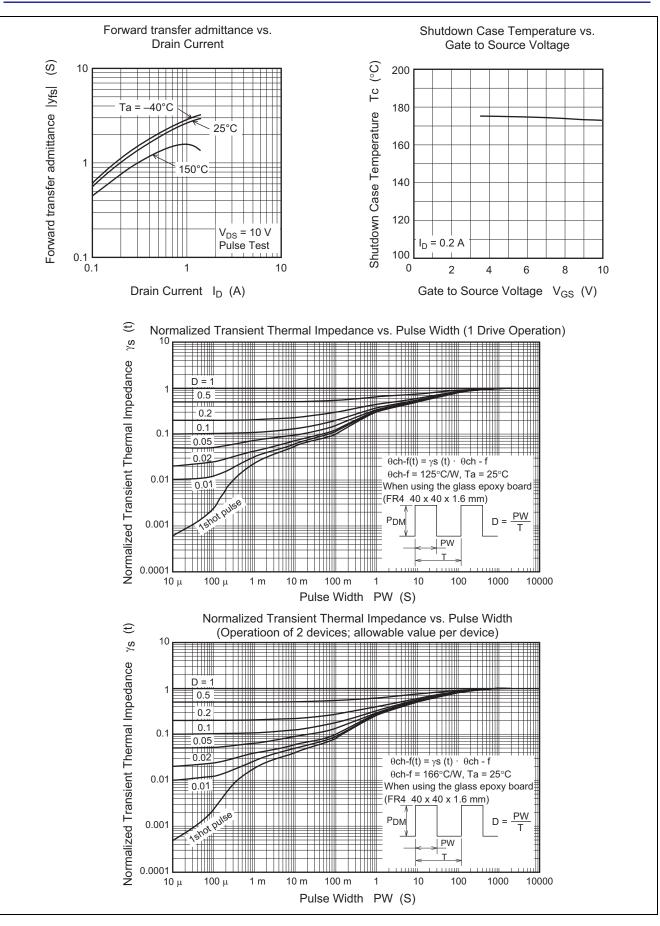
Main Characteristics

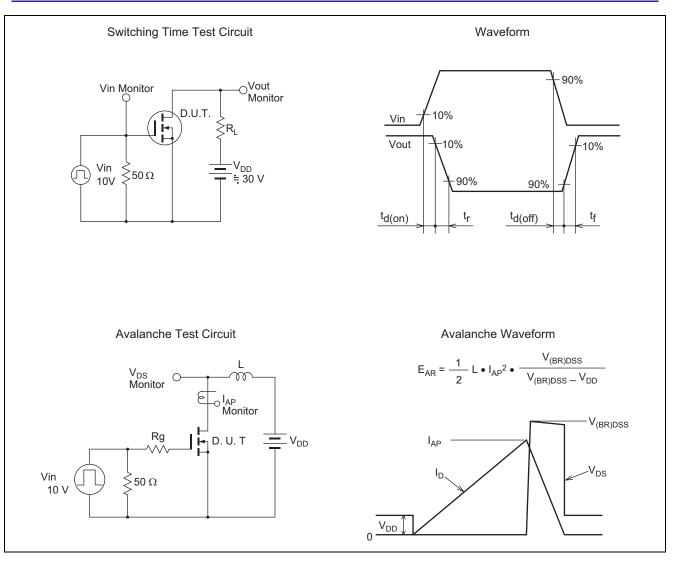






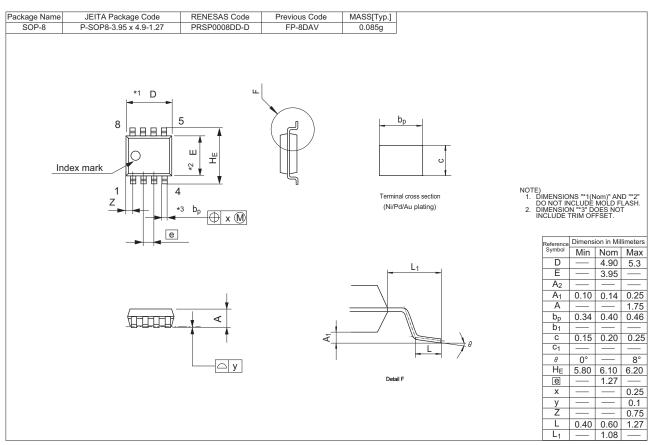








Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container		
RJF0609JSP-00-J0	2500 pcs/reel	Taping		

Note: The symbol of 2nd "-" is occasionally presented as "#".



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